

P-Channel MOSFET with 0.12V Schottky Diode

DESCRIPTION

BL8593 is designed for battery charging controller, which features P-channel MOSFET characteristics and a 0.12V Schottky diode for reverse current blocking. Such reverse current blocking feature cut off the current when source voltage is removed, or lower than drain voltage, no matter the gate voltage indicating the P-MOSFET on or off.

BL8593 is also suitable for high side switch in a system with multi power supplies, when isolating different power supplies becomes essential.

BL8593 can block reverse voltage as high as 10V. So it is safe enough for mobile phone system or other portable device powered by 1 cell Li-ion battery.

BL8593 is available in DFN2x2-6L (2 type of PIN configuration), SC70-5 and DFN1x1-5. Especially with the package DFN1x1-5, BL8593 make itself the smallest package available in the world.

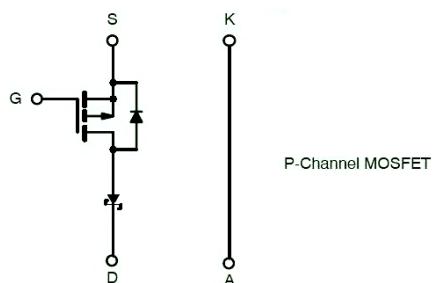
FEATURES

- PMOSFET with SBD for reverse current blocking
- 0.12V Schottky diode forward voltage
- Range of operation input voltage: Max 12V
- Charging current up to 650mA
- Environment Temperature: -20°C~85°C

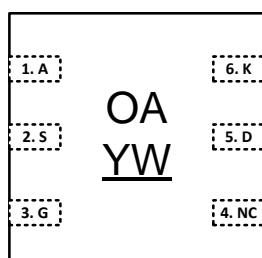
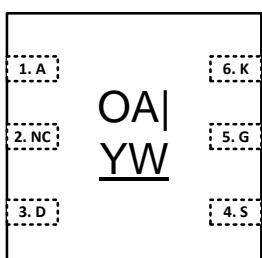
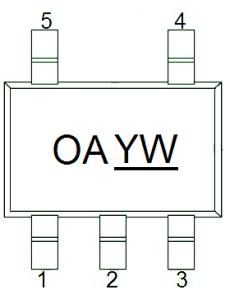
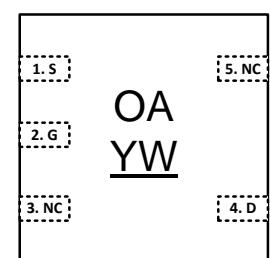
APPLICATIONS

- Cell phone and other portable device

FUNCTION DIAGRAM



ORDERING INFORMATION / PIN CONFIGURATION / MARKING

BL8593CKCTR DFN2x2-6L (compatible to DFN2x3 pin out)	BL8593CBKCTR DFN2x2-6L (compatible to DFN2x2 pin out)	BL8593CA5TR SC70-5	BL8593CKDTR DFN1x1-5L
			

Notice: YW means the year and week parts being manufactured, subjected to change. OA is the code of the product, it will not be changed on any part.

ABSOLUTE MAXIMUM RATING

Parameter	Symbol	5 sec	Steady State	Unit	
Forward Voltage(Source-Drain)	V_{SD}	12	$-8\text{~}+0.3$	V	
Gate-Source Voltage (MOSFET)	V_{GS}	-8~+0.3	-8~+0.3		
Continuous Drain Current	I_D	0.8	0.5	mA	
Pulsed Drain Current (MOSFET)	I_{DM}	1		A	
Maximum Power Dissipation	P_D	1	0.5	W	
Operating Junction Temperature Range	T_J	-20 to 125		°C	
Storage Temperature Range	T_{stg}	-40 to 150			
Soldering Recommendations (Peak Temperature)		260°C, 10s			

THERMAL RESISTANCE RATING

Parameter	Device	Symbol	Typical	Maximum	Unit
junction-to-Ambient	t ≤ 5 sec	DFN2x2	R _{thJA}	50	60
		DFN1x1		77	95
		SC70-5		250	280
	Steady State	DFN2x2		105	120
		DFN1x1		160	200
		SC70-5		330	400
Junction to Case	Steady State	DFN2x2	R _{thJC}	20	30
		DFN1x1		33	40
		SC70-5		150	175

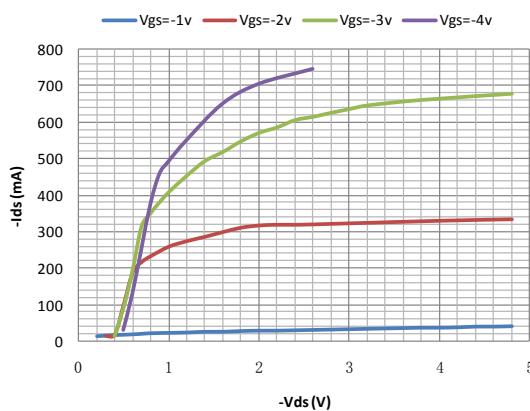
ELECTRICAL CHARACTERISTICST_j=25°C

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{th}	Threshold Voltage	I _{ds} =-10uA, V _{ds} =V _{gs}	-1.0	-0.7	-0.4	V
I _{gs}	Gate-Source Leakage current	V _{gs} =8V	0	12	20	uA
I _{Dss1}	PMOS off-state leakage	V _{gs} =0, V _s =9V, V _d =0V		0.5	5	uA
I _{Dss2}	PMOS reverse block leakage	V _g =0, V _s =0V, V _d =4.5V		2	10	uA
I _{dson}	On –state drain current	V _s =5V, V _g =1V, V _d =4V	-800	-650	-500	mA
R _{dson}	V _{ds} /I _{dson}	V _s =5V, V _g =1V, V _d =4V	1.25	1.5	2	ohm
V _{fsbd}	Forward voltage of schottky	V _s =4V, V _g =0V, I _{ds} =0,	0.08	0.12	0.16	V

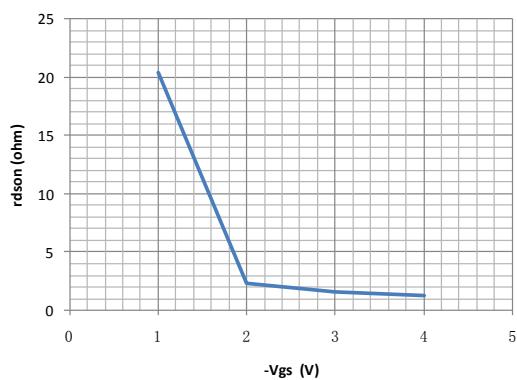
TYPICAL PERFORMANCE CHARACTERISTICS

T=25°C unless specified.

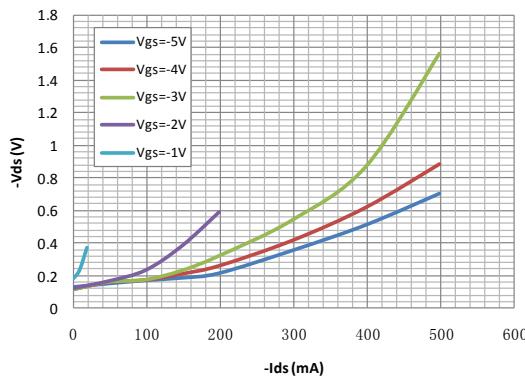
Output Characteristics



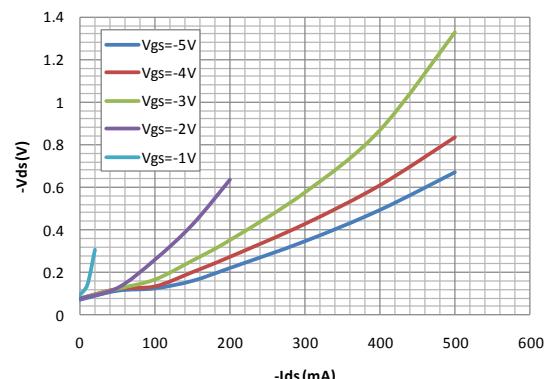
On Resistance Vs Vgs



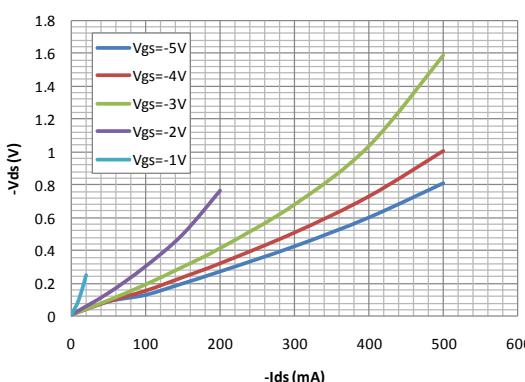
Dropout Voltage (V_{ds}) Vs. Charge current (Id_s), $T = 25^\circ C$



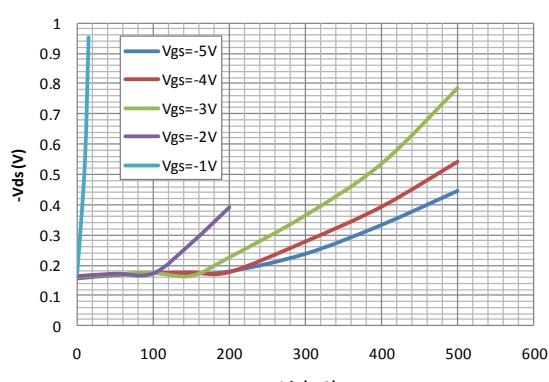
Dropout Voltage (V_{ds}) Vs. Charge current (Id_s), $T = 80^\circ C$



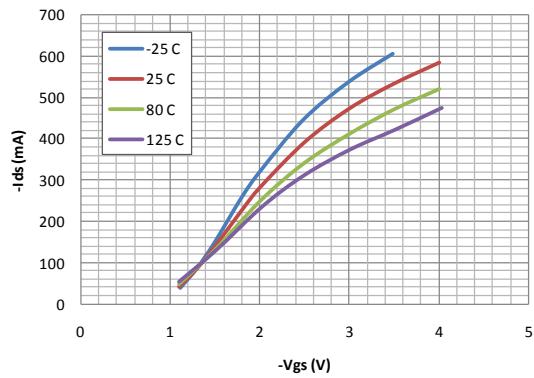
Dropout Voltage (V_{ds}) Vs. Charge current (Id_s), $T = 125^\circ C$



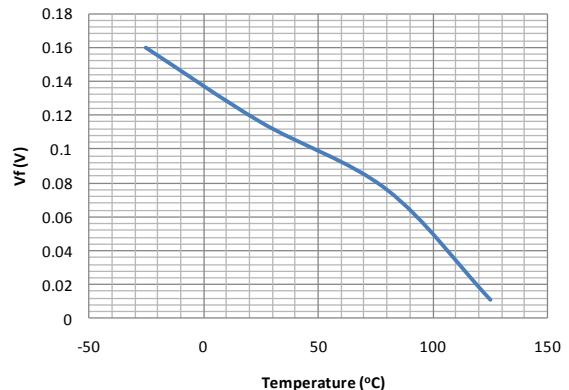
Dropout Voltage (V_{ds}) Vs. Charge current (Id_s), $T = -25^\circ C$



Charge Current (I_{ds}) Vs. Gate Voltage

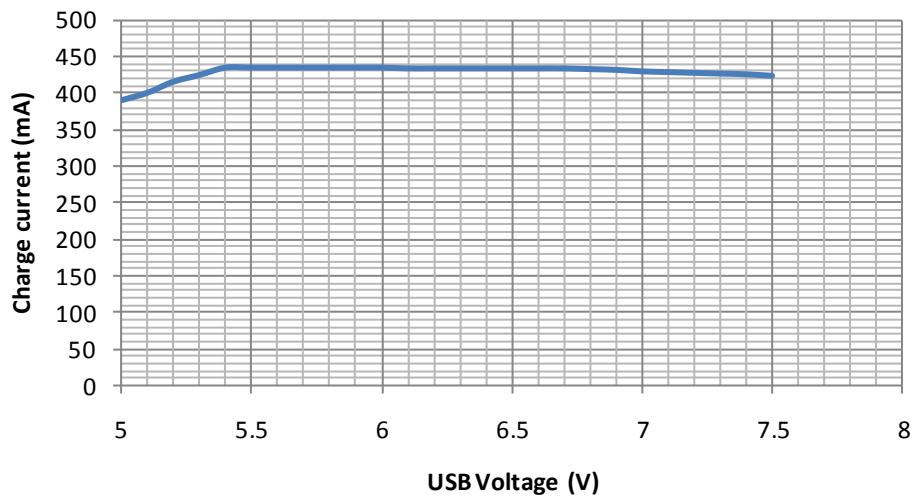


Schottky Diode Forward Voltage

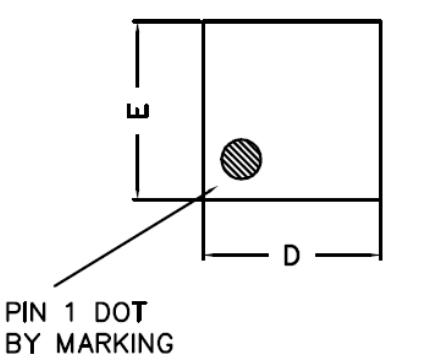
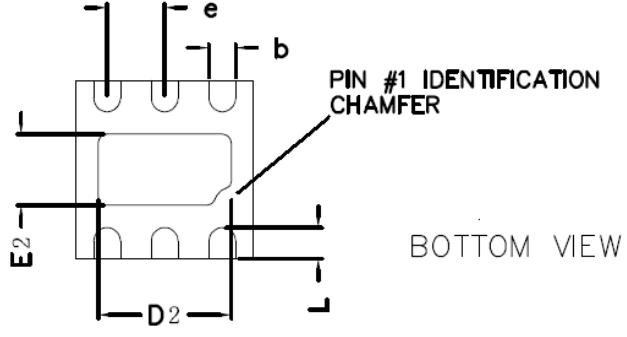
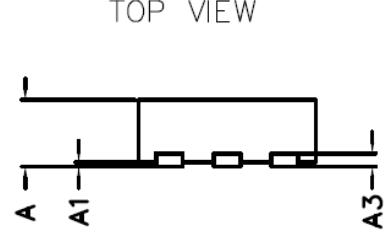
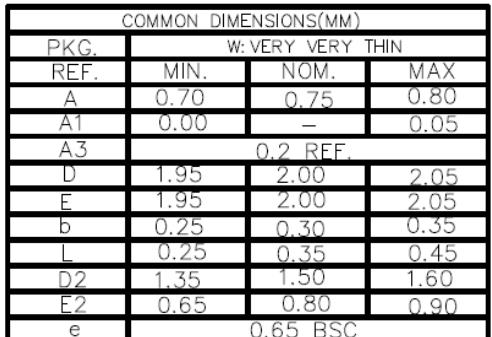
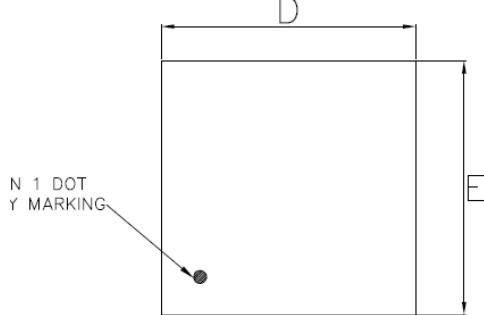
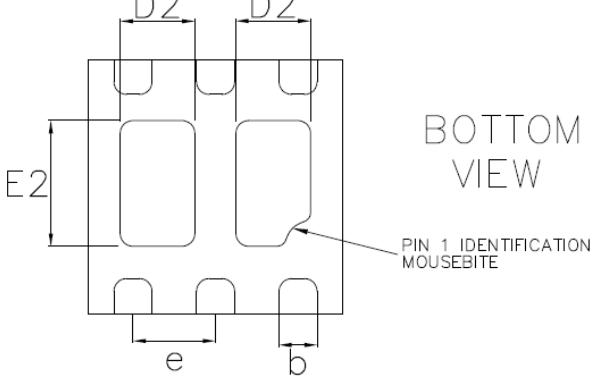
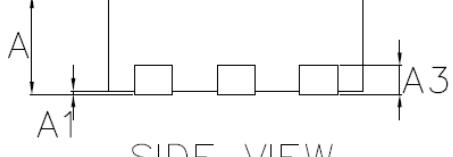
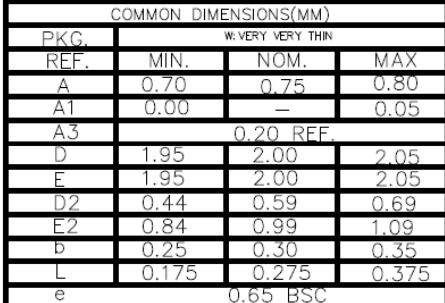


Charge current Vs USB voltage tested on actual cell phone powered by MTK chipset

I_{charge}

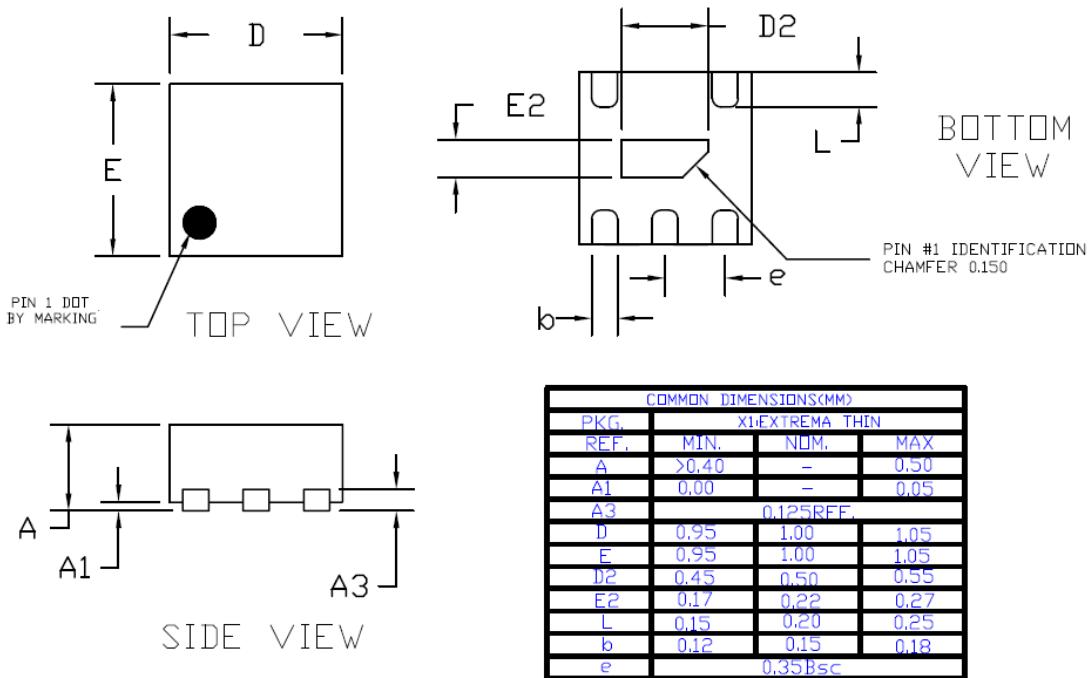


PACKAGE OUTLINE

Package	DFN2x2-6 single pad	Devices per reel	3000	Unit	mm
Package specification:					
					
	PIN 1 DOT BY MARKING	PIN #1 IDENTIFICATION CHAMFER			BOTTOM VIEW
					TOP VIEW
	SIDE VIEW				
Package	DFN2x2-6 dual pad	Devices per reel	3000	Unit	mm
Package specification:					
					
	N 1 DOT Y MARKING	PIN 1 IDENTIFICATION MOUSEBITE			BOTTOM VIEW
					TOP VIEW
	SIDE VIEW				

Package	DFN1x1-5	Devices per reel	3000	Unit	mm
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Package specification:



Package	SC70-5	Devices per reel	3000	Unit	mm
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Package specification:

